

# Sticking coefficients in Atomic Layer Deposition processes

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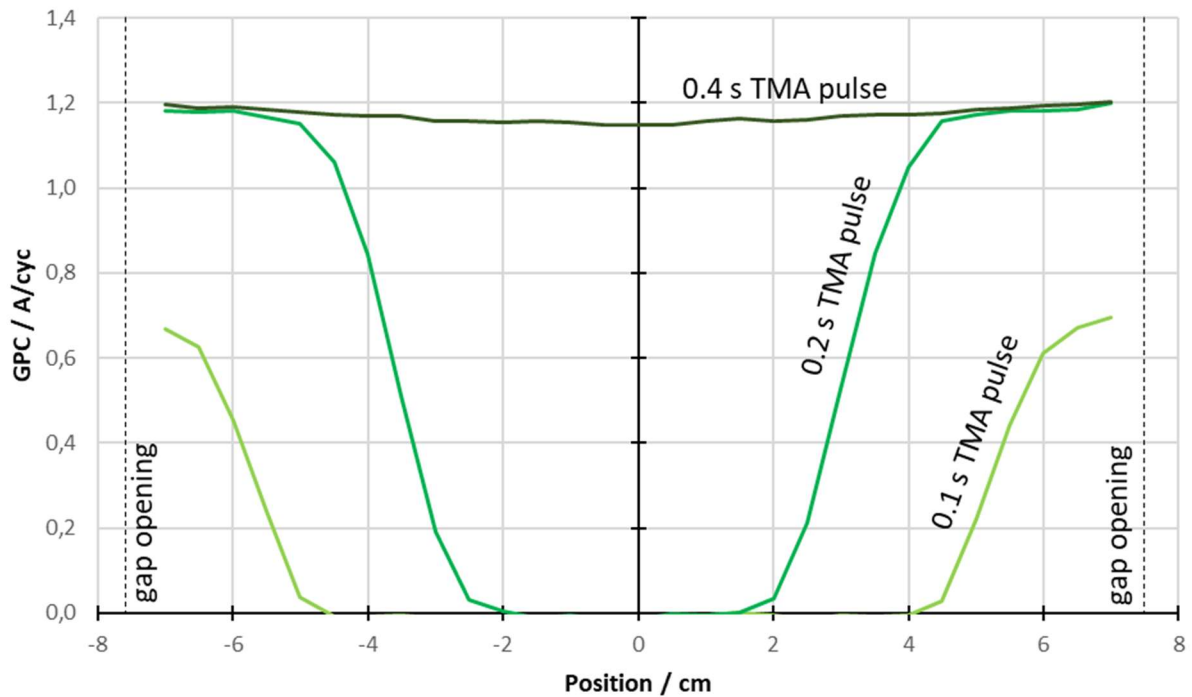


Fig. 1 – ALD  $\text{Al}_2\text{O}_3$  film growth characteristics with a high sticking coefficient in a 1 mm gap limited by the TMA precursor dose and extracted from Spectroscopic Ellipsometry maps of the deposited film thickness profiles

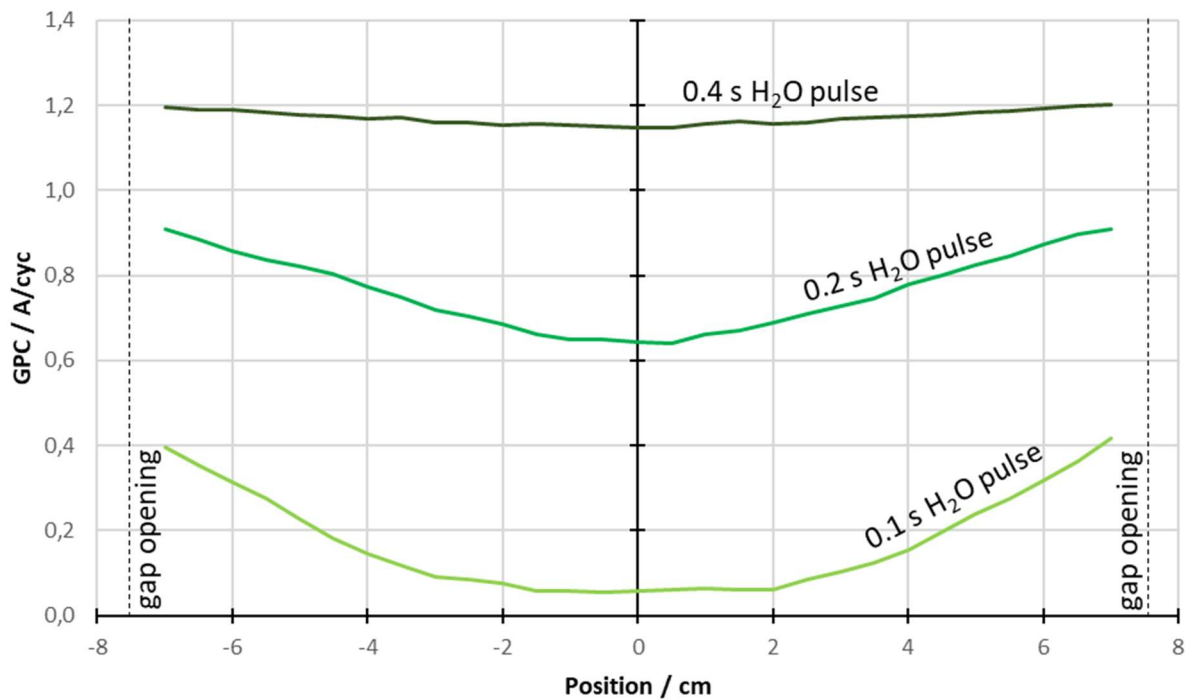


Fig. 2 – ALD  $\text{Al}_2\text{O}_3$  film growth characteristics with a low sticking coefficient in a 1 mm gap limited by the  $\text{H}_2\text{O}$  precursor dose and extracted from Spectroscopic Ellipsometry maps of the deposited film thickness profiles